

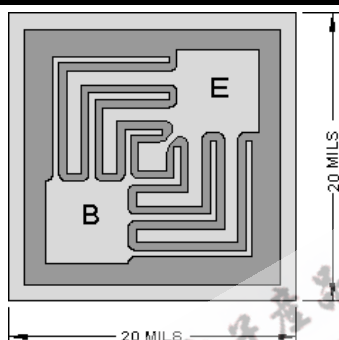


Data Sheet No. 2C2222A

Chip Type 2C2222A
Geometry 0400
Polarity NPN

Generic Packaged Parts:

2N2219, 2N2219A, 2N2222,
2N2222A



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Chip type **2C2222A** by Semicoa Semiconductors provides performance similar to these devices.

Part Numbers:

2N2222A, 2N2222, 2N2219, 2N2219A, 2N2219AL,
2N2222AUB, SD2222A, SD2222AF, SQ2222A,
SQ2222AF, 2N5582, 2N6989, 2N6990

Product Summary:

APPLICATIONS: Designed for general purpose switching and amplifier applications.

Features: Medium power ratings

Mechanical Specifications

Metallization	Top	Al - 24 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	4.0 mils x 4.0 mils
	Base	4.0 mils x 4.0 mils
Die Thickness	8 mils nominal	
Chip Area	20 mils x 20 mils	
Top Surface	Silox Passivated	

Electrical Characteristics

$T_A = 25^{\circ}\text{C}$

Parameter	Test conditions	Min	Max	Unit
BV_{CEO}	$I_C = 10\text{ mA}$, $I_B = 0$	40	---	V dc
BV_{CBO}	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$	75	---	V dc
BV_{EBO}	$I_E = 10\text{ }\mu\text{A}$, $I_C = 0$	6.0	---	V dc
I_{CBO}	$V_{CB} = 50\text{ V}$, $I_E = 0$	---	10	nA dc
h_{FE}	$I_C = 150\text{ mA dc}$, $V_{CE} = 10\text{ V}$	100	300	---

Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300 μs , duty cycle less than 2%.